



# isc Silicon NPN Power Transistor

## **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
- : V<sub>(BR)CEO</sub>= 150V(Min)
- · Wide Area of Safe Operation
- · Complement to Type 2SB1362
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

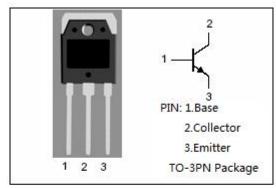


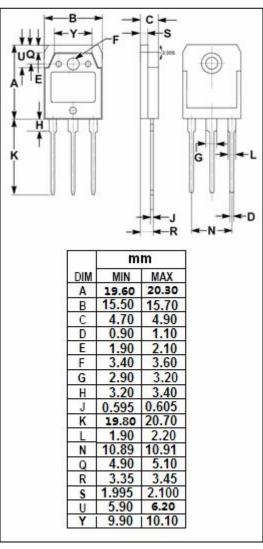
## **APPLICATIONS**

· Designed for high power amplifications.

# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>СВО</sub>	Collector-Base Voltage	150	V	
$V_{\text{CEO}}$	Collector-Emitter Voltage	150	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	9	Α	
I <sub>CP</sub>	Collector Current-Pulse	15	Α	
Pc	Collector Power Dissipation @ $T_c$ =25 $^{\circ}$ C	100	W	
	Collector Power Dissipation @ T <sub>a</sub> =25℃	2.5		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range -55~150		$^{\circ}$	







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2SD2053

#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 0.7A			2.0	V
V <sub>BE(on)</sub>	Base -Emitter On Voltage	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V			1.8	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 150V; I <sub>E</sub> = 0			50	μ <b>А</b>
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 3V; I <sub>C</sub> = 0			50	μ <b>А</b>
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 20mA; V <sub>CE</sub> = 5V	20			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	60		200	
h <sub>FE-3</sub>	DC Current Gain	I <sub>C</sub> = 7A; V <sub>CE</sub> = 5V	20			
fτ	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5 V; f= 1MHz		20		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1MHz		150		pF

## ♦ h<sub>FE-2</sub>Classifications

Q	S	Р
60-120	80-160	100-200

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